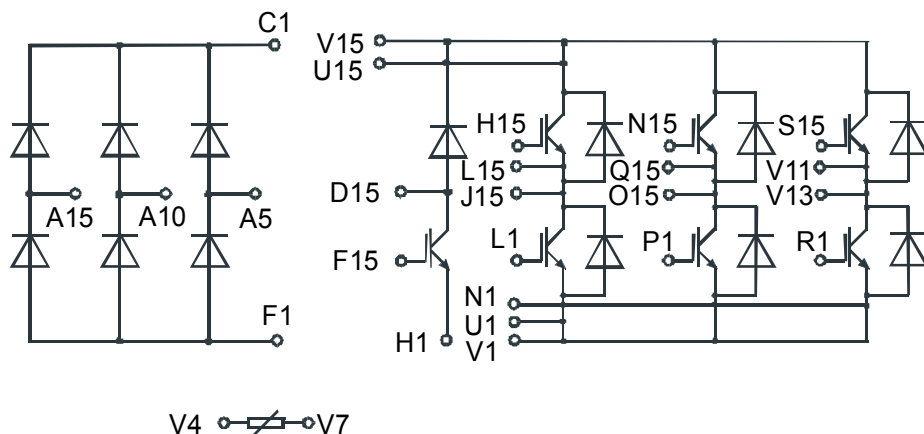


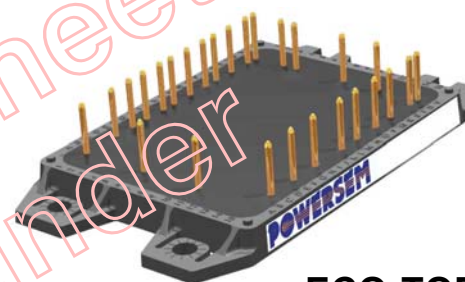
Converter - Brake - Inverter Module

Preliminary Data Sheet

PSIPM 100/06



Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{FAVM} = 68 \text{ A}$	$I_{C25} = 69 \text{ A}$	$I_{C25} = 121 \text{ A}$
$I_{FSM} = 300 \text{ A}$	$V_{CE(sat)} = 2.3 \text{ V}$	$V_{CE(sat)} = 2.3 \text{ V}$



ECO-TOP™ 1

Input Rectifiers

Symbol	Test Conditions	Maximum Ratings
I_{dAV}^*	$T_C = 100^\circ\text{C}$, (per circuit)	68 A
I_{FSM}	$T_{VJ} = 25^\circ\text{C}$; $t = 10 \text{ ms}$; $\sin 50 \text{ Hz}$	300 A
V_{RRM}		1600 V

Symbol	Test Conditions	Characteristic Value
I_R	$V_R = V_{RRM}$, $T_{VJ} = T_{VJM}$	$\leq 3 \text{ mA}$
	$V_R = V_{RRM}$, $T_{VJ} = 25^\circ\text{C}$	$\leq 0.5 \text{ mA}$
V_F	$I_F = 55 \text{ A}$, $T_{VJ} = 25^\circ\text{C}$	$\leq 1.46 \text{ V}$
V_{TO}	For power-loss calculations only	0.8 V
r_T		13 $\text{m}\Omega$
R_{thJC}	per diode; DC	1.1 K/W

Features

- Package with DCB ceramic base plate
- High level of integration - only one power semiconductor module required for the whole drive
- Planar glass passivated chips
- NPT IGBT technology with low saturation voltage, low switching losses, high RBSOA and short circuit ruggedness
- Epitaxial free wheeling diodes with hipfast and soft reverse recovery
- Temperature sense included
- Leads suitable for PC board soldering
- UL Release applied

Application: AC motor drives with

- Input from single or three phase grid
- Three phase synchronous or asynchronous motor
- Electric braking operations

Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

Output Inverter IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	121	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	83	A
I_{CM}	$V_{GE} = \pm 15\text{ V}; R_G = 2.2\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100\ \mu\text{H}$	200	A
V_{CEK}		360	V
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15\text{ V}; R_G = 2.2\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	379	W

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 130\text{ A}; V_{GE} = 15\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.3 2.6	2.9 V V
$V_{GE(th)}$	$I_C = 1.5\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			1.2 mA 7.5 mA
I_{GES}	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			400 nA
$t_{d(on)}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300\text{ V}; I_C = 80\text{ A}$ $V_{GE} = 15/0\text{ V}; R_G = 2.2\ \Omega$		25	ns
t_r			11	ns
$t_{d(off)}$			150	ns
t_f			30	ns
E_{on}			0.8	mJ
E_{off}			2.3	mJ
C_{ies}	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		4.2	nF
R_{thJC}	(per IGBT)			0.33 K/W

Output Inverter Reverse Diodes (FRED)

Symbol	Conditions	Maximum Ratings		
I _{F25}	T _C = 25°C	134.0	A	
I _{F80}	T _C = 80°C	82.3	A	
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 80 A; T _{VJ} = 25°C T _{VJ} = 125°C		1.85 1.40	2.06 V V
I _{RM} t _{rr}	} I _F = 60 A; di _F /dt = 500 A/μs; T _{VJ} = 125°C V _R = 300 V; V _{GE} = 0 V		28 100	A ns
R _{thJC}				0.66

Brake Chopper IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	69	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	48	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15\text{ V}; R_G = 22\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100\ \mu\text{H}$	100 V_{CES}	A
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15\text{ V}; R_G = 22\ \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	208	W

Symbol	Conditions	Characteristic Values		
		(T _{VJ} = 25°C, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 75\text{ A}; V_{GE} = 15\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.3 2.8	2.8 V
$V_{GE(th)}$	$I_C = 1\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			0.8 mA 4.4 mA
I_{GES}	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	$\left. \begin{array}{l} \text{Inductive load, } T_{VJ} = 125^{\circ}\text{C} \\ V_{CE} = 300\text{ V}; I_C = 40\text{ A} \\ V_{GE} = 15/0\text{ V}; R_G = 22\ \Omega \end{array} \right\}$		50 55 300 30 1.8 1.4	ns ns ns ns mJ mJ
C_{ies}	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		2.8	nF
R_{thJC}	(per IGBT)			0.6 K/W

Brake Chopper Diode (FRED)

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^{\circ}\text{C}$	56	A
I_{F80}	$T_C = 80^{\circ}\text{C}$	35	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 40\text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.32 1.58	2.59 V V
I_{RM} t_{rr}	$\left. \begin{array}{l} I_F = 30\text{ A}; di_F/dt = 500\text{ A}/\mu\text{s}; T_{VJ} = 125^{\circ}\text{C} \\ V_R = 300\text{ V}; V_{GE} = 0\text{ V} \end{array} \right\}$		15 70	A ns
R_{thJC}				1.3 K/W

Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^{\circ}\text{C}$	4.75	5.0	5.25 $\text{k}\Omega$
$B_{25/50}$			3375	K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+125	$^{\circ}\text{C}$
T_{stg}		-40...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	3 26	Nm lb.in.
a	Max. allowable acceleration	50	m/s^2

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight		86		g

Package style and outline

Dimensions in mm (1mm = 0.0394")

